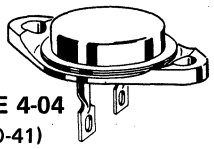
2N1120 (GERMANIUM)



CASE 4-04
(TO-41)

PNP germanium power transistor for military and industrial power applications.

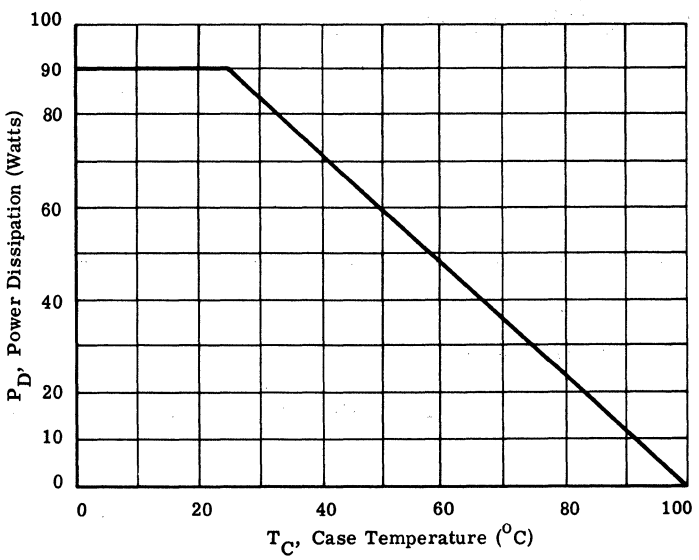
MAXIMUM RATINGS

Rating	Symbol	2N1120	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Emitter Voltage	V_{CES}	70	Vdc
Collector-Base Voltage	V_{CB}	80	Vdc
Emitter-Base Voltage	V_{EB}	40	Vdc
Emitter Current	I_E	15	Adc
Total Device Dissipation @ $T_C = 25^oC$ Derate above 25^oC	P_D	90 1.2	Watts $W/^oC$
Operating Junction Temperature Range	T_J	-65 to +100	^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	0.8	$^oC/W$

POWER-TEMPERATURE DERATING CURVE



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 300 mAdc, I_B = 0)	BV_{CEO}	40	-	Vdc
Collector-Emitter Breakdown Voltage (I_C = 300 mAdc, V_{BE} = 0)	BV_{CES}	70	-	Vdc
Floating Potential (V_{CB} = 80 Vdc, I_E = 0) (Voltmeter Input Resistance = 10 meg. min.)	V_{EBF}	-	1.0	Vdc
Collector Cutoff Current (V_{CB} = 2 Vdc, I_E = 0)	I_{CBO}	-	0.3	mAdc
(V_{CB} = 30 Vdc, I_E = 0)			20	
(V_{CB} = 80 Vdc, I_E = 0)		-	15	
Emitter Cutoff Current (V_{BE} = 40 Vdc, I_C = 0)	I_{EBO}	-	5.0	mAdc
Base Current (V_{CE} = 2 Vdc, I_C = 5 Adc)	I_B	50	-	mAdc
(V_{CE} = 2 Vdc, I_C = 10 Adc)		200	500	
ON CHARACTERISTICS				
DC Current Gain (I_C = 5.0 Adc, V_{CE} = 2.0 Vdc)	h_{FE}	-	100	-
(I_C = 10.0 Adc, V_{CE} = 2.0 Vdc)		20	50	
Collector-Emitter Saturation Voltage (I_C = 10 Adc, I_B = 1.0 Adc)	$V_{CE(sat)}$	-	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 Adc, I_B = 1.0 Adc)	$V_{BE(sat)}$	-	1.5	Vdc
Base-Emitter On Voltage (I_C = 10 Adc, V_{CE} = 2 Vdc)	$V_{BE(on)}$	-	2.0	Vdc
SMALL SIGNAL CHARACTERISTICS				
Common-Emitter Cutoff Frequency (I_C = 5.0 Adc, V_{CE} = 2.0 Vdc)	$f_{\alpha e}$	3.0	-	kHz